# LOW RESISTANCE METAL INTERCONNECT LINES AND A PROCESS FOR FABRICATING THEM

## ABSTRACT OF THE DISCLOSURE

Low resistance interconnect lines and methods for fabricating them are described herein. IC fabrication processes are used to create interconnect lines of Al and Cu layers. The Cu layer is thinner than in the known art, but in combination with the Al layer, the aggregate Cu/Al resistance is lowered to a point where it is comparable to that of a very thick Cu layer, without the additional cost and yield problems caused by using a thicker Cu deposition. Fuses for memory repair can also be fabricated using the methods taught by the present invention with only small variations in the process.